AMENDMENT TO THE CLAIMS

- 1. (Currently amended) A method of adding an electron to a first chemical substance, wherein said first chemical substance in a non-gaseous state is deposited onto a surface, said first chemical substance optionally being on the surface along with a second chemical substance, wherein:
- (a) said electron being is released from:
- (al) said surface, after exposure of said surface to light, said light having an energy which is below the work function of said surface or
- (\$\frac{1}{2}\$) said second chemical substance, after exposure of said surface or second chemical substance to light having an energy which is below the work function of said surface, and

 (b) said electron is added to said first chemical substance on said surface.
- 2. (Currently amended) The method of claim 1 wherein said surface is a metal surfacesaid substance in a non-gaseous state is deposited onto a metal surface, said-surface furnishing said electron, and said electron moving from said surface to said substance after exposure of said surface to light, said light having an energy which is below the work function of said surface.

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3. (Currently amended) The method of claim 2-in-which said

chemical substance is the first of two different chemical

substances deposited on said surface, said surface furnishing said

electron to said second chemical substance in an intermediate

step, and said electron moving from said second chemical substance

to said first chemical substance, said surface giving up said

electron after exposure of said surface to light.

4. (Currently amended) The method of claim 1 in which the

exposure of said second chemical substance to light results in

generation of said electron which is furnished to said first

chemical substance, wherein said second chemical substance has an

ionization potential of less than 8 electron volts.

5. (Currently amended) A method for detecting an analyte via

laser desorption mass spectrometry, wherein said analyte in a non-

gaseous state is deposited onto a surface, said analyte optionally

being on the surface along with a second chemical substance,

wherein

(a) an electron is added to said analyte on said surface, said

electron being released from:

- (all) said surface, after exposure of said surface to light, said light having an energy which is below the work function of said surface or
- (b2) said second chemical substance, after exposure of said surface or second chemical substance to light having an energy which is below the work function of said surface, and

 (b) said analyte having said added electron is desorbed from said surface and detected using laser desorption mass spectrometry.
- 6. (Currently amended) The method of claim 5, wherein said analyte in a non-gaseous state is deposited onto a metal surface, said surface furnishing said electron, and said electron moving from said surface to said <u>second chemical</u> substance after exposure of said surface to light, said light having an energy which is below the work function of said surface.
- 7. (Currently amended) The method of claim 6—in—which said analyte is the first of two different chemical substances deposited on said surface, said surface furnishing said electron to said second chemical substance in an intermediate step, and said electron moving from said second chemical substance to said first chemical substance analyte, said surface giving up said electron after exposure of said surface to light.

8. (Original) The method of claim 7 in which the exposure of said second substance to light results in generation of said electron which is furnished to said analyte, wherein said second chemical substance has an ionization potential of less than 8 electron volts.

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- 9. (Currently amended) The method of claim 5 in which said analyte, prior to capturing an electron, contains an anionic part or group.
- 10. (Original) The method of claim 5 in which said analyte has a mass of greater than 300 atomic mass units.
- 11. (Currently amended) The method of claim 5 in which said analyte comprises a biomolecule, drug or drug candidate polyfluoro organic group.
- 12. (Currently amended) The method of claim 11 5 wherein said biomolecule analyte is a nucleic acid or a protein.
- 13. (Original) The method of claim 5 in which said analyte contains nitrogen or oxygen.

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- 14. (Original) The method of claim 5 in which said light is from a laser having a wavelength of greater than or equal to 300 nm.
- 15. (Original) The method of claim 14 in which said wavelength is 337 or 355 nm.
- 16. (Currently amended) The method of claim 5 wherein the power density of said light te-has a power density of ≥10⁵ watts per square centimeter.
- 17. (Currently amended) The method of claim 5 wherein said analyte is a salt—analyte, and the and the entity being desorbed is the anion part of said salt is desorbed.
- 18. (Original) The method of claim 5 in which said analyte comprises a polyfluoro-containing group.
- 19. (Original) The method of claim 18 in which said polyfluoro-containing group is a polyfluoro-phenyl group.

- 20. (Currently amended) The method of claim 8 in which <u>said</u> ionization potential of said second substance has an ionization potential of less than 7.5 electron volts.
- 21. (Original) The method of claim 12 in which said protein or nucleic acid comprises a polyfluoro group.
- 22. (Original) The method of claim 5 in which said surface comprises silver.
- 23. (Original) The method of claim 5 in which said surface comprises indium.
- 24. (Original) The method of claim 5 in which said surface comprises gold.
- 25. (Original) The method of claim 5 in which said analyte is covalently bonded to said surface.
- 26. (Original) The method of claim 9 wherein said analyte comprises a polyfluoro-containing group.

- 27. (Original) The method of claim 5 wherein said surface is not polished.
- 28. (Currently amended) The method of claim 5 wherein said energy of said light has an energy-which is below the work function of said surface by more than 0.4 eV.
- 29. (Original) The method of claim 5 wherein said light has an energy below 4.0 eV.